



## Subject card

Subject name and code	Electronic Devices - laboratory, PG_00048812						
Field of study	Electronics and Telecommunications						
Date of commencement of studies	October 2021		Academic year of realisation of subject		2022/2023		
Education level	first-cycle studies		Subject group		Obligatory subject group in the field of study Subject group related to scientific research in the field of study		
Mode of study	Full-time studies		Mode of delivery		at the university		
Year of study	2		Language of instruction		Polish		
Semester of study	4		ECTS credits		1.0		
Learning profile	general academic profile		Assessment form		assessment		
Conducting unit	Department of Microelectronic Systems -> Faculty of Electronics, Telecommunications and Informatics						
Name and surname of lecturer (lecturers)	Subject supervisor		dr inż. Łukasz Gołuński				
	Teachers		dr inż. Łukasz Gołuński mgr inż. Krzysztof Zwolski dr hab. inż. Piotr Płotka dr hab. inż. Waldemar Jendernalik				
Lesson types and methods of instruction	Lesson type	Lecture	Tutorial	Laboratory	Project	Seminar	SUM
	Number of study hours	0.0	0.0	15.0	0.0	0.0	15
	E-learning hours included: 0.0						
Learning activity and number of study hours	Learning activity	Participation in didactic classes included in study plan		Participation in consultation hours		Self-study	SUM
	Number of study hours	15		1.0		9.0	25
Subject objectives	Learning through experiments of the operation principles of basic semiconductor devices and learning the methods of measuring their characteristics, as well as learning methods of determining values of their equivalent circuits, useful in designing of electronic circuits.						

Learning outcomes	Course outcome	Subject outcome	Method of verification
	[K6_U06] can analyse the operation of components, circuits and systems related to the field of study, measure their parameters and examine technical specifications	Student measures and analyzes static characteristics of diodes and transistors. Student measures and analyzes processes of switching in circuits with diodes. Student measures and analyzes processes of switching in circuits with transistors. Student measures and analyzes small signal amplifying properties of transistors in dependence on frequency. Student measures characteristics and analyzes properties of electroluminescent diodes. Student measures characteristics and analyzes properties of photodiodes, photoelements and optical relays.	[SU1] Assessment of task fulfilment [SU4] Assessment of ability to use methods and tools
	[K6_U05] can plan and conduct experiments related to the field of study, including computer simulations and measurements; interpret obtained results and draw conclusions	Student measures and analyzes static characteristics of diodes and transistors. Student measures and analyzes processes of switching in circuits with diodes. Student measures and analyzes processes of switching in circuits with transistors. Student measures and analyzes small signal amplifying properties of transistors in dependence on frequency. Student measures characteristics and analyzes properties of electroluminescent diodes. Student measures characteristics and analyzes properties of photodiodes, photoelements and optical relays.	[SU1] Assessment of task fulfilment [SU4] Assessment of ability to use methods and tools
Subject contents	Static characteristics of semiconductor diodes. Switching characteristics of semiconductor diodes. Properties of stabilization diodes. IV characteristics of field effect transistors and extraction of parameters for their equivalent circuits. Small signal operation of transistors for small and medium frequencies. Pulse operation and models of transistors. Characteristics and models of electroluminescent diodes and photodiodes.		
Prerequisites and co-requisites			
Assessment methods and criteria	Subject passing criteria	Passing threshold	Percentage of the final grade
	Laboratory experiments	50.0%	100.0%
Recommended reading	Basic literature	Our laboratory instruction booklets.  Ch. Papadopoulos, "Solid-State Electronic Devices: An Introduction", Springer 2014  J.-P. Colinge, C.A. Colinge, "Physics of Semiconductor Devices", Springer 2002	
	Supplementary literature	A.S. Sedra, K.C. Smith, "Microelectronic Circuits", Oxford, 2007  Ch.C. Hu, Modern Semiconductor Devices for Integrated Circuits, Prentice Hall 2009	
	eResources addresses	Adresy na platformie eNauczanie:	
Example issues/ example questions/ tasks being completed	Connect a circuit presented on a diagram in the instruction booklet. The output voltage value of the generator should be adjusted so that the peak-peak value of Vce is 100 mV at f = 1 kHz. Take a record of the generator voltage Vgpp. Use it to calculate the low-frequency value of h21e0. Measure and plot the dependence of  h21e  on frequency. Determine experimentally the fbeta value. Calculate values of the emitter-base diffusion capacitance CdifE, the common-emitter current-gain cut-off frequency fT, and the electron transit time ttn.		
Work placement	Not applicable		